

## **APPLICATION DATA SHEET**

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Attorney Docket Number: XDEV1100

**Application Type:** 

utility

Title of Invention:

CONTACT METHOD FOR THIN SILICON CARBIDE EPITAXIAL LAYER AND SEMICONDUCTOR DEVICES FORMED BY THOSE METHODS

[Request Not To Publish:]

**Attorney Docket Number:** 

XDEV1100

**Customer Number Attorney:** 

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**Customer Number Correspondence Address:** 

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